

SN74LVC1G34 Single Buffer Gate

1 Features

- Available in the ultra small 0.64mm² package (DPW) with 0.5mm pitch
- Supports 5V V_{CC} operation
- Inputs accept voltages to 5.5V
- Provides down translation to V_{CC}
- Maximum t_{pd} of 3.5ns at 3.3V
- Low power consumption, 1µA maximum I_{CC}
- ±24mA output drive at 3.3V
- I_{off} supports live insertion, partial power down mode, and back drive protection
- Latch-up performance exceeds 100mA per JESD 78, Class II
- ESD protection exceeds JESD 22
 - 2000V human-body model (A114-A)
 - 200V machine model (A115-A)
 - 1000V charged-device model (C101)

2 Applications

- AV receiver
- Audio dock: portable
- Blu-ray player and home theater
- DVD recorder and player
- Embedded PC
- MP3 player/recorder (portable audio)
- Personal Digital Assistant (PDA)
- Power: telecom/server AC/DC supply: single controller: analog and digital
- Solid State Drive (SSD): client and enterprise
- TV: LCD/digital and high-definition (HDTV)
- Tablet: enterprise
- Video analytics: server
- Wireless headset, keyboard, and mouse

3 Description

This single buffer gate is designed for 1.65V to 5.5V V_{CC} operation.

The SN74LVC1G34 device performs the Boolean function Y = A in positive logic.

The CMOS device has high output drive while maintaining low static power dissipation over a broad V_{CC} Operating range.

The SN74LVC1G34 is available in a variety of packages, including the ultra-small DPW package with a body size of 0.8mm × 0.8mm.

Package Information

	i donago ii		
DEVICE NAME	PACKAGE (1)	PACKAGE SIZE ⁽²⁾	BODY SIZE (NOM) ⁽³⁾
	YFP (DSBGA, 4)	1.00mm ×1.00mm	0.76mm × 0.76mm
	YZP (DSBGA, 5)	1.75mm × 1.25mm	1.38mm × 0.88mm
	YZV (DSBGA, 4)	1.25mm × 1.25mm	0.88mm × 0.88mm
	DPW (X2SON, 5)	0.80mm × 0.80mm	0.80mm × 0.80mm
SN74LVC1G34	DBV (SOT-23, 5)	2.90mm × 2.80mm	2.90mm × 2.80mm
	DCK (SC70, 5)	2.00mm × 2.10mm	2.00mm × 2.10mm
	DRL (SOT, 5)	1.60mm × 1.60mm	1.60mm × 1.60mm
	DRY (USON (6)	1.45mm ×1.00mm	1.45mm ×1.00mm
	DSF (X2SON, 6)	1.00mm × 1.00mm	1.00mm × 1.00mm

- For all available packages, see the orderable addendum at (1) the end of the datasheet.
- The package size (length × width) is a nominal value and includes pins, where applicable.
- The body size (length × width) is a nominal value and does not include pins.

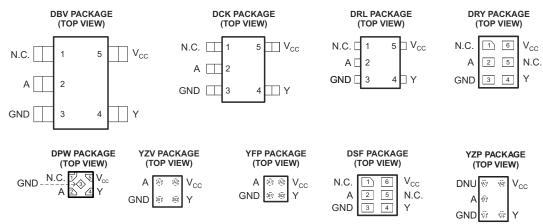




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4 Pin Configuration and Functions



See mechanical drawings for dimensions.

N.C. – No internal connection

DNU – Do not use

Table 4-1. Pin Functions

		PIN								
NAME	DRL, DCK, DBV	DPW	DRY, DSF	YZP	YFP, YZV	DESCRIPTION				
NC	1	1	1, 5	A1	_	Not connected				
Α	2	2	2	B1	A1	Input				
GND	3	3	3	C1	B1	Ground				
Y	4	4	4	C2	B2	Output				
V _{CC}	5	5	6	A2	A2	Power pin				



5 Specifications

5.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)

(1)			MIN	MAX	UNIT
V _{CC}	Supply voltage range		-0.5	6.5	V
VI	Input voltage range	-0.5	6.5	V	
Vo	Voltage range applied to any output in the high-impedar	nce or power-off state ⁽²⁾	-0.5	6.5	V
Vo	Voltage range applied to any output in the high or low st	ate ^{(2) (3)}	-0.5	V _{CC} + 0.5	V
I _{IK}	Input clamp current	V _I < 0		-50	mA
I _{OK}	Output clamp current	V _O < 0		-50	mA
Io	Continuous output current			±50	mA
	Continuous current through V _{CC} or GND			±100	mA
T _{stg}	Storage temperature range		-65	150	°C
T _J	Max Junction temperature			150	°C

⁽¹⁾ Stresses beyond those listed under Absolute Maximum Ratings may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under Recommended Operating Conditions is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

5.2 ESD Ratings

			MIN	MAX	UNIT
V	Electrostatic discharge	Human body model (HBM), per ANSI/ESDA/JEDEC JS-001, all pins ⁽¹⁾		±2	kV
V _(ESD)	Liectiostatic discharge	Charged device model (CDM), per JEDEC specification JESD22-C101, all pins ⁽²⁾		±1	ΝV

(1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.

(2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

²⁾ The input and output negative-voltage ratings may be exceeded if the input and output current ratings are observed.

⁽³⁾ The value of V_{CC} is provided in the Recommended Operating Conditions table.

5.3 Recommended Operating Conditions

(1)			MIN	MAX	UNIT
.,	Cumplicitation	Operating	1.65	5.5	V
V _{CC}	Supply voltage	Data retention only	1.5		V
		V _{CC} = 1.65 V to 1.95 V	0.65 × V _{CC}		
\	High lovel input veltage	V _{CC} = 2.3 V to 2.7 V	1.7		V
V _{IH}	High-level input voltage	V _{CC} = 3 V to 3.6 V	2		V
		V _{CC} = 4.5 V to 5.5 V	0.7 × V _{CC}		
		V _{CC} = 1.65 V to 1.95 V		0.35 × V _{CC}	
\	Low level input valtage	V _{CC} = 2.3 V to 2.7 V		0.7	V
V_{IL}	Low-level input voltage	V _{CC} = 3 V to 3.6 V		0.8	V
		V _{CC} = 4.5 V to 5.5 V		0.3 × V _{CC}	
VI	Input voltage		0	5.5	V
Vo	Output voltage		0	V _{CC}	V
		V _{CC} = 1.65 V		-4	
		V _{CC} = 2.3 V		-8	
I _{OH}	High-level output current	V _{CC} = 3 V		-16	mA
		VCC - 3 V		-24	
		V _{CC} = 4.5 V		-32	
		V _{CC} = 1.65 V		4	
		V _{CC} = 2.3 V		8	
I_{OL}	Low-level output current	V _{CC} = 3 V		16	mA
		VCC - 3 V		24	
		V _{CC} = 4.5 V		32	
		V _{CC} = 1.8 V ± 0.15 V, 2.5 V ± 0.2 V		20	
∆t/∆v	Input transition rise or fall rate	V _{CC} = 3.3 V ± 0.3 V		10	ns/V
		$V_{CC} = 5 V \pm 0.5 V$		10	
T _A	Operating free-air temperature	DSBGA package	-40	85	°C
		All other packages	-40	125	°C

⁽¹⁾ All unused inputs of the device must be held at V_{CC} or GND to ensure proper device operation. Refer to the TI application report, *Implications of Slow or Floating CMOS Inputs*, literature number SCBA004.

5.4 Thermal Information

			SN74LVC1G34							
	THERMAL METRIC(1)	DBV	DCK	DRL	DRY	YZP	DPW	UNIT		
		5 PINS	5 PINS	5 PINS	6 PINS	5 PINS	4 PINS			
R _{θJA}	Junction-to-ambient thermal resistance	357.1	278	243	439	130	340			
R _{0JC(top)}	Junction-to-case (top) thermal resistance	263.7	93	78	277	54	215			
R _{θJB}	Junction-to-board thermal resistance	264.4	65	78	271	51	294	°C/W		
ΨЈТ	Junction-to-top characterization parameter	195.6	2	10	84	1	41	- C/VV		
ΨЈВ	Junction-to-board characterization parameter	262.2	64	77	271	50	294			
R _{0JC(bot)}	Junction-to-case (bottom) thermal resistance	-	_	-	_	-	250			

⁽¹⁾ For more information about traditional and new thermal metrics, see the Semiconductor and IC Package Thermal Metrics application note.



5.5 Electrical Characteristics

over recommended operating free-air temperature range (unless otherwise noted)

DADAMETED	TEGT COMPLETIONS	.,	-40°C to 85°C		-40°C	to 125°C		UNIT		
PARAMETER	TEST CONDITIONS	V _{cc}	MIN	TYP ⁽¹⁾	MAX	MIN	TYP ⁽¹⁾	MAX	UNII	
	I _{OH} = -100 μA	1.65 V to 5.5 V	V _{CC} - 0.1			V _{CC} - 0.1				
	I _{OH} = –4 mA	1.65 V	1.2			1.2				
\ /	I _{OH} = -8 mA	2.3 V	1.9			1.9			V	
V_{OH}	I _{OH} = -16 mA	3 V	2.4			2.4			V	
	I _{OH} = -24 mA		2.3			2.3				
	I _{OH} = -32 mA	4.5 V	3.8			3.8				
	I _{OL} = 100 μA	1.65 V to 5.5 V			0.1			0.1		
	I _{OL} = 4 mA	1.65 V			0.45			0.45		
V_{OL}	I _{OL} = 8 mA	2.3 V			0.3			0.3	V	
V OL	I _{OL} = 16 mA	3 V			0.4			0.4	V	
	I _{OL} = 24 mA				0.55			0.55		
	I _{OL} = 32 mA	4.5 V			0.55			0.55		
I _I	V _I = 5.5 V or GND	0 to 5.5 V			±1			±2	μA	
l _{off}	V _I or V _O = 5.5 V	0			±10			±10	μA	
Icc	$V_1 = 5.5 \text{ V or GND}, I_0 = 0$	1.65 V to 5.5 V			1			10	μA	
ΔI _{CC}	One input at $V_{CC} - 0.6 \text{ V}$, Other inputs at V_{CC} or GND	3 V to 5.5 V			500			500	μА	
C_{i}	V _I = V _{CC} or GND	3.3 V		3.5					pF	

⁽¹⁾ All typical values are at V_{CC} = 3.3 V, T_A = 25°C.

5.6 Switching Characteristics, C_L = 15 pF

over recommended operating free-air temperature range, C_L = 15 pF (unless otherwise noted) (see Figure 6-1)

						-40°C 1	to 85°C				
PARAMETER	FROM (INPUT)	TO (OUTPUT)	V _{CC} = 1.8 V ± 0.15 V		V _{CC} = 2.5 V ± 0.2 V		V _{CC} = 3.3 V ± 0.3 V		V _{CC} = 5 V ± 0.5 V		UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
t _{pd}	A	Y	2	9.9	1.5	6	1	3.5	1	2.9	ns

5.7 Switching Characteristics, -40°C to 85°C

over recommended operating free-air temperature range, $C_L = 30 \text{ pF}$ or 50 pF (unless otherwise noted) (see Figure 6-2)

						-40°C	to 85°C				
PARAMETER	FROM (INPUT)	TO (OUTPUT)	V _{CC} = 1.8 V ± 0.15 V		V _{CC} = 2.5 V ± 0.2 V		V _{CC} = 3.3 V ± 0.3 V		V _{CC} = 5 V ± 0.5 V		UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
t _{pd}	Α	Y	3.2	8.6	1.5	4.4	1.5	4.1	1	3.2	ns

5.8 Switching Characteristics, -40°C to 125°C

over recommended operating free-air temperature range, C_L = 30 pF or 50 pF (unless otherwise noted) (see Figure 6-2)

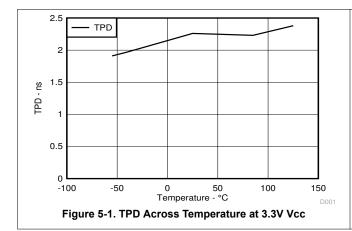
						–40°C t	o 125°C				
PARAMETER	FROM (INPUT)	TO (OUTPUT)	V _{CC} = 1.8 V ± 0.15 V		V _{CC} = 2.5 V ± 0.2 V		V _{CC} = 3.3 V ± 0.3 V		V _{CC} = 5 V ± 0.5 V		UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
t _{pd}	A	Y	3.2	9.5	1.5	5.1	1.5	4.7	1	3.9	ns

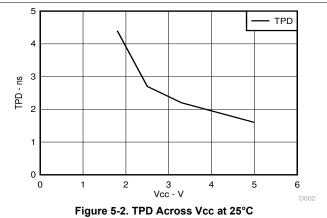
5.9 Operating Characteristics

 $T_A = 25^{\circ}C$

, ,							
PARAMETER		TEST	V _{CC} = 1.8 V	V _{CC} = 2.5 V	V _{CC} = 3.3 V	V _{CC} = 5 V	UNIT
	FARAMETER	CONDITIONS	TYP	TYP	TYP	TYP	ONII
C_{pd}	Power dissipation capacitance	f = 10 MHz	16	16	16	18	pF

5.10 Typical Characteristics



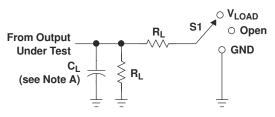


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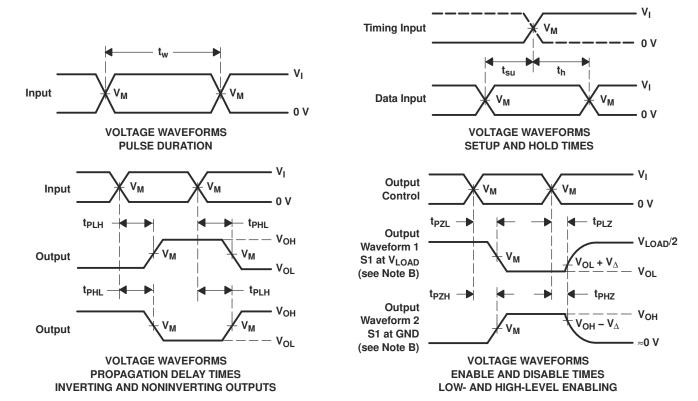
6 Parameter Measurement Information



TEST	S1
t _{PLH} /t _{PHL}	Open
t _{PLZ} /t _{PZL}	V _{LOAD}
t _{PHZ} /t _{PZH}	GND

		:UIT

V	INI	PUTS	.,	V			V	
V _{CC}	V _I t _r /t _f		V _M	V _{LOAD}	CL	RL	V_Δ	
1.8 V \pm 0.15 V	V _{CC}	≤2 ns	V _{CC} /2	2×V _{CC}	15 pF	1 Μ Ω	0.15 V	
2.5 V \pm 0.2 V	v_{cc}	≤2 ns	V _{CC} /2	2 × V _{CC}	15 pF	1 Μ Ω	0.15 V	
3.3 V \pm 0.3 V	3 V	≤2.5 ns	1.5 V	6 V	15 pF	1 Μ Ω	0.3 V	
5 V \pm 0.5 V	v_{cc}	≤2.5 ns	V _{CC} /2	2 × V _{CC}	15 pF	1 Μ Ω	0.3 V	

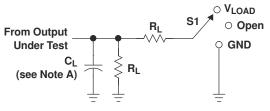


- NOTES: A. C_L includes probe and jig capacitance.
 - B. Waveform 1 is for an output with internal conditions such that the output is low, except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high, except when disabled by the output control.
 - C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω.
 - D. The outputs are measured one at a time, with one transition per measurement.
 - E. t_{PLZ} and t_{PHZ} are the same as t_{dis} .
 - F. t_{PZL} and t_{PZH} are the same as t_{en}.
 - G. t_{PLH} and t_{PHL} are the same as t_{pd} .
 - H. All parameters and waveforms are not applicable to all devices.

Figure 6-1. Load Circuit and Voltage Waveforms

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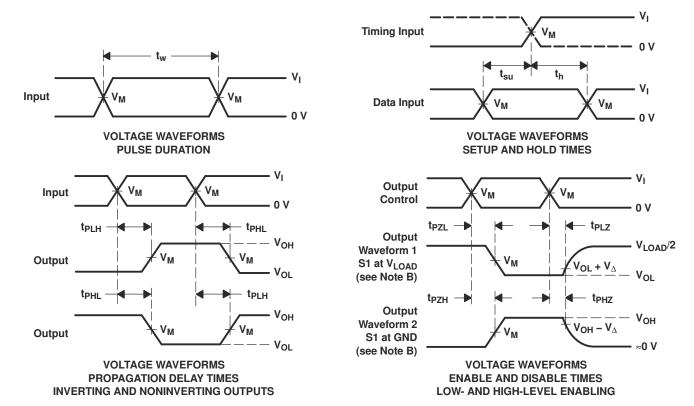
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TEST	S1
t _{PLH} /t _{PHL}	Open
t _{PLZ} /t _{PZL}	V _{LOAD}
t _{PHZ} /t _{PZH}	GND

LOAD CIRCUIT

INPUT		PUTS	V	V	_	В	V
V _{CC}	VI	t _r /t _f	V _M	V _{LOAD}	CL	R _L	V_{Δ}
1.8 V ± 0.15 V	V _{CC}	≤2 ns	V _{CC} /2	2×V _{CC}	30 pF	1 k Ω	0.15 V
2.5 V \pm 0.2 V	V _{CC}	≤2 ns	V _{CC} /2	2 × V _{CC}	30 pF	500 Ω	0.15 V
3.3 V \pm 0.3 V	3 V	≤2.5 ns	1.5 V	6 V	50 pF	500 Ω	0.3 V
5 V \pm 0.5 V	V _{CC}	≤2.5 ns	V _{CC} /2	2 × V _{CC}	50 pF	500 Ω	0.3 V



- NOTES: A. C_L includes probe and jig capacitance.
 - B. Waveform 1 is for an output with internal conditions such that the output is low, except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high, except when disabled by the output control.
 - C. All input pulses are supplied by generators having the following characteristics: PRR \leq 10 MHz, $Z_0 = 50 \Omega$.
 - D. The outputs are measured one at a time, with one transition per measurement.
 - E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
 - F. t_{PZL} and t_{PZH} are the same as t_{en}.
 - G. t_{PLH} and t_{PHL} are the same as t_{pd} .
 - H. All parameters and waveforms are not applicable to all devices.

Figure 6-2. Load Circuit and Voltage Waveforms

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7 Detailed Description

7.1 Overview

The SN74LVC1G34 device contains one buffer gate device and performs the Boolean function Y = A. This device is fully specified for partial-power-down applications using I_{off} . The I_{off} circuitry disables the outputs, preventing damaging current backflow through the device when it is powered down.

7.2 Functional Block Diagram



7.3 Feature Description

7.4 Device Functional Modes

Function Table

INPUT A	OUTPUT Y
Н	Н
L	L



8 Application and Implementation

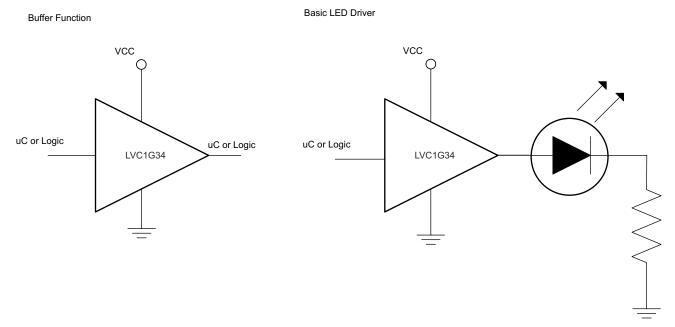
Note

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes, as well as validating and testing their design implementation to confirm system functionality.

8.1 Application Information

The SN74LVC1G34 is a high drive CMOS device that can be used as a buffer to drive an LED. It can produce 24 mA of drive current at 3.3 V making it ideal for driving multiple outputs and good for high speed applications up to 100 MHz.

8.2 Typical Application



8.2.1 Design Requirements

8.2.1.1 Power Considerations

Ensure the desired supply voltage is within the range specified in the *Recommended Operating Conditions*. The supply voltage sets the device's electrical characteristics of the device as described in the *Electrical Characteristics* section.

The positive voltage supply must be capable of sourcing current equal to the maximum static supply current, I_{CC}, listed in the *Electrical Characteristics*, and any transient current required for switching.

The ground must be capable of sinking current equal to the total current to be sunk by all outputs of the SN74LVC1G34 plus the maximum supply current, I_{CC}, listed in the *Electrical Characteristics*, and any transient current required for switching. The logic device can only sink as much current that can be sunk into its ground connection. Ensure the maximum total current through GND listed in the *Absolute Maximum Ratings* is not exceeded.

The SN74LVC1G34 can drive a load with a total capacitance less than or equal to 50pF while still meeting all of the data sheet specifications. Larger capacitive loads can be applied; however, it is not recommended to exceed 50pF.

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The SN74LVC1G34 can drive a load with total resistance described by $R_L \ge V_O / I_O$, with the output voltage and current defined in the *Electrical Characteristics* table with V_{OL} . When outputting in the HIGH state, the output voltage in the equation is defined as the difference between the measured output voltage and the supply voltage at the V_{CC} pin.

Total power consumption can be calculated using the information provided in *CMOS Power Consumption and Cpd Calculation*.

Thermal increase can be calculated using the information provided in *Thermal Characteristics of Standard Linear* and Logic (SLL) Packages and Devices.

CAUTION

The maximum junction temperature, $T_{J(max)}$ listed in the *Absolute Maximum Ratings*, is an additional limitation to prevent damage to the device. Do not violate any values listed in the *Absolute Maximum Ratings*. These limits are provided to prevent damage to the device.

8.2.1.2 Input Considerations

Input signals must cross to be considered a logic LOW, and to be considered a logic HIGH. Do not exceed the maximum input voltage range found in the *Absolute Maximum Ratings*.

Unused inputs must be terminated to either V_{CC} or ground. The unused inputs can be directly terminated if the input is completely unused, or they can be connected with a pull-up or pull-down resistor if the input will be used sometimes, but not always. A pull-up resistor is used for a default state of HIGH, and a pull-down resistor is used for a default state of LOW. The drive current of the controller, leakage current into the SN74LVC1G34 (as specified in the *Electrical Characteristics*), and the desired input transition rate limits the resistor size. A $10k\Omega$ resistor value is often used due to these factors.

Refer to the *Feature Description* section for additional information regarding the inputs for this device.

8.2.1.3 Output Considerations

The ground voltage is used to produce the output LOW voltage. Sinking current into the output will increase the output voltage as specified by the V_{OI} specification in the *Electrical Characteristics*.

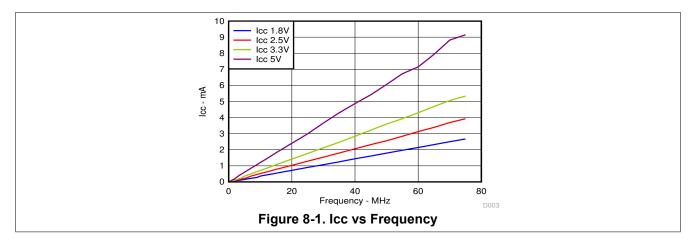
Unused outputs can be left floating. Do not connect outputs directly to V_{CC} or ground.

Refer to the *Feature Description* section for additional information regarding the outputs for this device.

8.2.1.4 Detailed Design Procedure

- Add a decoupling capacitor from V_{CC} to GND. The capacitor needs to be placed physically close to the device and electrically close to both the V_{CC} and GND pins. An example layout is shown in the *Layout* section.
- 2. Ensure the capacitive load at the output is ≤ 50pF. This is not a hard limit; by design, however, it will optimize performance. This can be accomplished by providing short, appropriately sized traces from the SN74LVC1G34 to one or more of the receiving devices.
- 3. Ensure the resistive load at the output is larger than $(V_{CC} / I_{O(max)})\Omega$. Doing this will prevent the maximum output current from the *Absolute Maximum Ratings* from being violated. Most CMOS inputs have a resistive load measured in M Ω ; much larger than the minimum calculated previously.
- 4. Thermal issues are rarely a concern for logic gates; the power consumption and thermal increase, however, can be calculated using the steps provided in the application report, *CMOS Power Consumption and Cpd Calculation*.

8.2.2 Application Curves



8.3 Power Supply Recommendations

The power supply can be any voltage between the minimum and maximum supply voltage rating located in the *Recommended Operating Conditions*. Each V_{CC} terminal should have a good bypass capacitor to prevent power disturbance. A $0.1\mu F$ capacitor is recommended for this device. It is acceptable to parallel multiple bypass capacitors to reject different frequencies of noise. The $0.1\mu F$ and $1\mu F$ capacitors are commonly used in parallel. The bypass capacitor should be installed as close to the power terminal as possible for best results.

8.4 Layout

8.4.1 Layout Guidelines

- Bypass capacitor placement
 - Place near the positive supply terminal of the device
 - Provide an electrically short ground return path
 - Use wide traces to minimize impedance
 - Keep the device, capacitors, and traces on the same side of the board whenever possible
- Signal trace geometry
 - 8mil to 12mil trace width
 - Lengths less than 12cm to minimize transmission line effects
 - Avoid 90° corners for signal traces
 - Use an unbroken ground plane below signal traces
 - Flood fill areas around signal traces with ground
 - Parallel traces must be separated by at least 3x dielectric thickness
 - For traces longer than 12cm
 - Use impedance controlled traces
 - · Source-terminate using a series damping resistor near the output
 - Avoid branches; buffer each signal that must branch separately



8.4.2 Layout Example

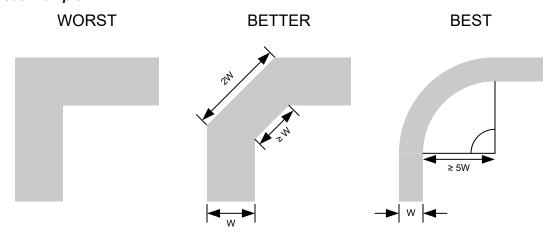


Figure 8-2. Example Trace Corners for Improved Signal Integrity

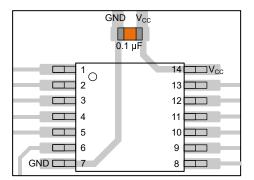


Figure 8-3. Example Bypass Capacitor Placement for TSSOP and Similar Packages

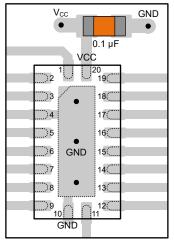


Figure 8-4. Example Bypass Capacitor Placement for WQFN and Similar Packages

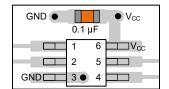


Figure 8-5. Example Bypass Capacitor Placement for SOT, SC70 and Similar Packages

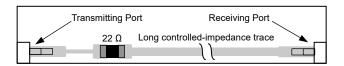


Figure 8-6. Example Damping Resistor Placement for Improved Signal Integrity

9 Device and Documentation Support

TI offers an extensive line of development tools. Tools and software to evaluate the performance of the device, generate code, and develop solutions are listed below.

9.1 Documentation Support

9.1.1 Related Documentation

For related documentation, see the following:

- Texas Instruments, CMOS Power Consumption and Cpd Calculation application report
- Texas Instruments, Designing With Logic application report
- Texas Instruments, Thermal Characteristics of Standard Linear and Logic (SLL) Packages and Devices application report

9.2 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on ti.com. Click on *Notifications* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

9.3 Support Resources

TI E2E[™] support forums are an engineer's go-to source for fast, verified answers and design help — straight from the experts. Search existing answers or ask your own question to get the quick design help you need.

Linked content is provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's Terms of Use.

9.4 Trademarks

TI E2E[™] is a trademark of Texas Instruments.

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9.5 Electrostatic Discharge Caution



This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

9.6 Glossary

TI Glossary

This glossary lists and explains terms, acronyms, and definitions.



10 Revision History

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

C	hanges from Revision M (April 2016) to Revision N (June 2025)	Page
•	Updated the numbering format for tables, figures, and cross-references throughout the document	1
•	Changed Device Information table to Package Information	1
•	Changed Junction-to-ambient thermal resistance value for DBV package from: 229°C/W to: 357.1°C/W	/ <mark>5</mark>
•	Changed Junction-to-case (top) thermal resistance value for DBV package from: 164°C/W to: 263.7°C/	/W <mark>5</mark>
•	Changed Junction-to-board thermal resistance value for DBV package from: 62°C/W to: 264.4°C/W	5
•	Changed Junction-to-top characterization value for DBV package from: 44°C/W to: 195.6°C/W	5
•	Changed Junction-to-board characterization value for DBV package from: 62°C/W to: 262.2°C/W	5
С	hanges from Revision L (April 2014) to Revision M (April 2016)	Page
•	Changed X2SON from 4 pin to 5 pin on Device Information table	1
•	Moved Storage temperature range from ESD Ratings table to Absolute Maximum Ratings table	4
•	Added Junction temperature to Absolute Maximum Ratings table	4
•	Added package temperature specification for DSBGA package	<mark>5</mark>

11 Mechanical, Packaging, and Orderable Information

The following pages include mechanical packaging and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

www.ti.com 30-Jun-2025

PACKAGING INFORMATION

Orderable part number	Status (1)	Material type	Package Pins	Package qty Carrier	RoHS	Lead finish/ Ball material	MSL rating/ Peak reflow	Op temp (°C)	Part marking (6)
SN74LVC1G34DBVR	Active	Production	SOT-23 (DBV) 5	3000 LARGE T&R	Yes	NIPDAU SN NIPDAU Level-1-260C-UNLIM		-40 to 125	(C345, C34F, C34J, C34K, C34R) (C34H, C34P, C34S)
SN74LVC1G34DBVR.A	Active	Production	SOT-23 (DBV) 5	3000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	(C345, C34F, C34J, C34K, C34R) (C34H, C34P, C34S)
SN74LVC1G34DBVR.B	Active	Production	SOT-23 (DBV) 5	3000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	(C345, C34F, C34J, C34K, C34R) (C34H, C34P, C34S)
SN74LVC1G34DBVRE4	Active	Production	SOT-23 (DBV) 5	3000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	C345 C34S
SN74LVC1G34DBVRG4	Active	Production	SOT-23 (DBV) 5	3000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	C345 C34S
SN74LVC1G34DBVRG4.B	Active	Production	SOT-23 (DBV) 5	3000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	C345 C34S
SN74LVC1G34DBVT	Active	Production	SOT-23 (DBV) 5	250 SMALL T&R	Yes	NIPDAU SN NIPDAU	Level-1-260C-UNLIM	-40 to 125	(C345, C34J, C34K, C34R) (C34H, C34S)
SN74LVC1G34DBVT.B	Active	Production	SOT-23 (DBV) 5	250 SMALL T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	(C345, C34J, C34K, C34R) (C34H, C34S)
SN74LVC1G34DBVTE4	Active	Production	SOT-23 (DBV) 5	250 SMALL T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	C345 C34S
SN74LVC1G34DBVTG4	Active	Production	SOT-23 (DBV) 5	250 SMALL T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	C345 C34S
SN74LVC1G34DBVTG4.B	Active	Production	SOT-23 (DBV) 5	250 SMALL T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	C345 C34S
SN74LVC1G34DCKR	Active	Production	SC70 (DCK) 5	3000 LARGE T&R	Yes	NIPDAU SN NIPDAU	Level-1-260C-UNLIM	-40 to 125	(C95, C9F, C9J, C9 R) (C9H, C9P, C9S)





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Orderable part number	Status (1)	Material type	Package Pins	Package qty Carrier	RoHS (3)	Lead finish/ Ball material	MSL rating/ Peak reflow	Op temp (°C)	Part marking (6)
SN74LVC1G34DCKR.A	Active	Production	SC70 (DCK) 5	3000 LARGE T&R	Yes	SN	Level-1-260C-UNLIM	-40 to 125	(C95, C9F, C9J, C9 R) (C9H, C9P, C9S)
SN74LVC1G34DCKR.B	Active	Production	SC70 (DCK) 5	3000 LARGE T&R	Yes	SN	Level-1-260C-UNLIM	-40 to 125	(C95, C9F, C9J, C9 R) (C9H, C9P, C9S)
SN74LVC1G34DCKRE4	Active	Production	SC70 (DCK) 5	3000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	C95 C9S
SN74LVC1G34DCKRG4	Active	Production	SC70 (DCK) 5	3000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	C95 C9S
SN74LVC1G34DCKRG4.A	Active	Production	SC70 (DCK) 5	3000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	C95 C9S
SN74LVC1G34DCKRG4.B	Active	Production	SC70 (DCK) 5	3000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	C95 C9S
SN74LVC1G34DCKT	Active	Production	SC70 (DCK) 5	250 SMALL T&R	Yes	NIPDAU SN NIPDAU	Level-1-260C-UNLIM	-40 to 125	(C95, C9J, C9R) (C9H, C9S)
SN74LVC1G34DCKT.B	Active	Production	SC70 (DCK) 5	250 SMALL T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	(C95, C9J, C9R) (C9H, C9S)
SN74LVC1G34DCKTG4	Active	Production	SC70 (DCK) 5	250 SMALL T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	C95 C9S
SN74LVC1G34DCKTG4.B	Active	Production	SC70 (DCK) 5	250 SMALL T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	C95 C9S
SN74LVC1G34DPWR	Active	Production	X2SON (DPW) 5	3000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	P4
SN74LVC1G34DPWR.B	Active	Production	X2SON (DPW) 5	3000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	P4
SN74LVC1G34DRLR	Active	Production	SOT-5X3 (DRL) 5	4000 LARGE T&R	Yes	NIPDAUAG	Level-1-260C-UNLIM	-40 to 125	(C97, C9R)
SN74LVC1G34DRLR.B	Active	Production	SOT-5X3 (DRL) 5	4000 LARGE T&R	Yes	NIPDAUAG	Level-1-260C-UNLIM	-40 to 125	(C97, C9R)
SN74LVC1G34DRYR	Active	Production	SON (DRY) 6	5000 LARGE T&R	Yes	NIPDAU NIPDAUAG	Level-1-260C-UNLIM	-40 to 125	C9
SN74LVC1G34DRYR.B	Active	Production	SON (DRY) 6	5000 LARGE T&R	Yes	NIPDAUAG	Level-1-260C-UNLIM	-40 to 125	C 9
SN74LVC1G34DRYRG4	Active	Production	SON (DRY) 6	5000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	C9
SN74LVC1G34DRYRG4.B	Active	Production	SON (DRY) 6	5000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	C9
SN74LVC1G34DSFR	Active	Production	SON (DSF) 6	5000 LARGE T&R	Yes	NIPDAU NIPDAUAG	Level-1-260C-UNLIM	-40 to 125	C9
SN74LVC1G34DSFR.B	Active	Production	SON (DSF) 6	5000 LARGE T&R	Yes	NIPDAUAG	Level-1-260C-UNLIM	-40 to 125	C9
SN74LVC1G34DSFRG4	Active	Production	SON (DSF) 6	5000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	C9
SN74LVC1G34DSFRG4.B	Active	Production	SON (DSF) 6	5000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	C9





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Orderable part number	Status (1)	Material type	Package Pins	Package qty Carrier	RoHS (3)	Lead finish/ Ball material	MSL rating/ Peak reflow	Op temp (°C)	Part marking (6)
						(4)	(5)		_
SN74LVC1G34YFPR	Active	Production	DSBGA (YFP) 4	3000 LARGE T&R	Yes	SNAGCU	Level-1-260C-UNLIM	-40 to 85	C9 N
SN74LVC1G34YFPR.B	Active	Production	DSBGA (YFP) 4	3000 LARGE T&R	Yes	SNAGCU	Level-1-260C-UNLIM	-40 to 85	C9 N
SN74LVC1G34YZPR	Active	Production	DSBGA (YZP) 5	3000 LARGE T&R	Yes	SNAGCU	Level-1-260C-UNLIM	-40 to 85	C9N
SN74LVC1G34YZPR.B	Active	Production	DSBGA (YZP) 5	3000 LARGE T&R	Yes	SNAGCU	Level-1-260C-UNLIM	-40 to 85	C9N
SN74LVC1G34YZVR	Active	Production	DSBGA (YZV) 4	3000 LARGE T&R	Yes	SNAGCU	Level-1-260C-UNLIM	-40 to 85	C9 N
SN74LVC1G34YZVR.B	Active	Production	DSBGA (YZV) 4	3000 LARGE T&R	Yes	SNAGCU	Level-1-260C-UNLIM	-40 to 85	C9 N

⁽¹⁾ Status: For more details on status, see our product life cycle.

Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "~" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.

Important Information and Disclaimer: The information provided on this page represents TI's knowledge and belief as of the date that it is provided. TI bases its knowledge and belief on information provided by third parties, and makes no representation or warranty as to the accuracy of such information. Efforts are underway to better integrate information from third parties. TI has taken and continues to take reasonable steps to provide representative and accurate information but may not have conducted destructive testing or chemical analysis on incoming materials and chemicals. TI and TI suppliers consider certain information to be proprietary, and thus CAS numbers and other limited information may not be available for release.

⁽²⁾ Material type: When designated, preproduction parts are prototypes/experimental devices, and are not yet approved or released for full production. Testing and final process, including without limitation quality assurance, reliability performance testing, and/or process qualification, may not yet be complete, and this item is subject to further changes or possible discontinuation. If available for ordering, purchases will be subject to an additional waiver at checkout, and are intended for early internal evaluation purposes only. These items are sold without warranties of any kind.

⁽³⁾ RoHS values: Yes, No, RoHS Exempt. See the TI RoHS Statement for additional information and value definition.

⁽⁴⁾ Lead finish/Ball material: Parts may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

⁽⁵⁾ MSL rating/Peak reflow: The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.

⁽⁶⁾ Part marking: There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.



PACKAGE OPTION ADDENDUM

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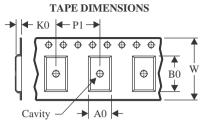
In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.



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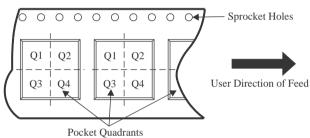
TAPE AND REEL INFORMATION





A0	Dimension designed to accommodate the component width
В0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
SN74LVC1G34DBVR	SOT-23	DBV	5	3000	180.0	8.4	3.2	3.2	1.4	4.0	8.0	Q3
SN74LVC1G34DBVR	SOT-23	DBV	5	3000	180.0	8.4	3.2	3.2	1.4	4.0	8.0	Q3
SN74LVC1G34DBVRG4	SOT-23	DBV	5	3000	178.0	9.2	3.3	3.23	1.55	4.0	8.0	Q3
SN74LVC1G34DBVT	SOT-23	DBV	5	250	180.0	8.4	3.23	3.17	1.37	4.0	8.0	Q3
SN74LVC1G34DBVT	SOT-23	DBV	5	250	178.0	9.0	3.3	3.2	1.4	4.0	8.0	Q3
SN74LVC1G34DBVT	SOT-23	DBV	5	250	178.0	9.2	3.3	3.23	1.55	4.0	8.0	Q3
SN74LVC1G34DBVTG4	SOT-23	DBV	5	250	178.0	9.2	3.3	3.23	1.55	4.0	8.0	Q3
SN74LVC1G34DCKR	SC70	DCK	5	3000	180.0	8.4	2.3	2.5	1.2	4.0	8.0	Q3
SN74LVC1G34DCKRG4	SC70	DCK	5	3000	178.0	9.2	2.4	2.4	1.22	4.0	8.0	Q3
SN74LVC1G34DCKT	SC70	DCK	5	250	180.0	8.4	2.47	2.3	1.25	4.0	8.0	Q3
SN74LVC1G34DCKT	SC70	DCK	5	250	178.0	9.2	2.4	2.4	1.22	4.0	8.0	Q3
SN74LVC1G34DCKT	SC70	DCK	5	250	178.0	9.0	2.4	2.5	1.2	4.0	8.0	Q3
SN74LVC1G34DCKTG4	SC70	DCK	5	250	178.0	9.2	2.4	2.4	1.22	4.0	8.0	Q3
SN74LVC1G34DPWR	X2SON	DPW	5	3000	178.0	8.4	0.91	0.91	0.5	2.0	8.0	Q3
SN74LVC1G34DRLR	SOT-5X3	DRL	5	4000	180.0	8.4	1.98	1.78	0.69	4.0	8.0	Q3
SN74LVC1G34DRYR	SON	DRY	6	5000	180.0	9.5	1.15	1.6	0.75	4.0	8.0	Q1



PACKAGE MATERIALS INFORMATION

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Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
SN74LVC1G34DRYRG4	SON	DRY	6	5000	180.0	9.5	1.15	1.6	0.75	4.0	8.0	Q1
SN74LVC1G34DSFR	SON	DSF	6	5000	180.0	9.5	1.16	1.16	0.5	4.0	8.0	Q2
SN74LVC1G34DSFRG4	SON	DSF	6	5000	180.0	9.5	1.16	1.16	0.5	4.0	8.0	Q2
SN74LVC1G34YFPR	DSBGA	YFP	4	3000	178.0	9.2	0.89	0.89	0.58	4.0	8.0	Q1
SN74LVC1G34YZPR	DSBGA	YZP	5	3000	178.0	9.2	1.02	1.52	0.63	4.0	8.0	Q1
SN74LVC1G34YZVR	DSBGA	YZV	4	3000	178.0	9.2	1.0	1.0	0.63	4.0	8.0	Q1



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*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
SN74LVC1G34DBVR	SOT-23	DBV	5	3000	210.0	185.0	35.0
SN74LVC1G34DBVR	SOT-23	DBV	5	3000	210.0	185.0	35.0
SN74LVC1G34DBVRG4	SOT-23	DBV	5	3000	180.0	180.0	18.0
SN74LVC1G34DBVT	SOT-23	DBV	5	250	202.0	201.0	28.0
SN74LVC1G34DBVT	SOT-23	DBV	5	250	180.0	180.0	18.0
SN74LVC1G34DBVT	SOT-23	DBV	5	250	180.0	180.0	18.0
SN74LVC1G34DBVTG4	SOT-23	DBV	5	250	180.0	180.0	18.0
SN74LVC1G34DCKR	SC70	DCK	5	3000	210.0	185.0	35.0
SN74LVC1G34DCKRG4	SC70	DCK	5	3000	180.0	180.0	18.0
SN74LVC1G34DCKT	SC70	DCK	5	250	202.0	201.0	28.0
SN74LVC1G34DCKT	SC70	DCK	5	250	180.0	180.0	18.0
SN74LVC1G34DCKT	SC70	DCK	5	250	180.0	180.0	18.0
SN74LVC1G34DCKTG4	SC70	DCK	5	250	180.0	180.0	18.0
SN74LVC1G34DPWR	X2SON	DPW	5	3000	205.0	200.0	33.0
SN74LVC1G34DRLR	SOT-5X3	DRL	5	4000	202.0	201.0	28.0
SN74LVC1G34DRYR	SON	DRY	6	5000	184.0	184.0	19.0
SN74LVC1G34DRYRG4	SON	DRY	6	5000	184.0	184.0	19.0
SN74LVC1G34DSFR	SON	DSF	6	5000	184.0	184.0	19.0



PACKAGE MATERIALS INFORMATION

www.ti.com 18-Jun-2025

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
SN74LVC1G34DSFRG4	SON	DSF	6	5000	184.0	184.0	19.0
SN74LVC1G34YFPR	DSBGA	YFP	4	3000	220.0	220.0	35.0
SN74LVC1G34YZPR	DSBGA	YZP	5	3000	220.0	220.0	35.0
SN74LVC1G34YZVR	DSBGA	YZV	4	3000	220.0	220.0	35.0



SMALL OUTLINE TRANSISTOR



NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
 2. This drawing is subject to change without notice.
 3. Reference JEDEC MO-178.

- 4. Body dimensions do not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.25 mm per side.
- 5. Support pin may differ or may not be present.



SMALL OUTLINE TRANSISTOR



NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



SMALL OUTLINE TRANSISTOR



NOTES: (continued)

- 8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 9. Board assembly site may have different recommendations for stencil design.



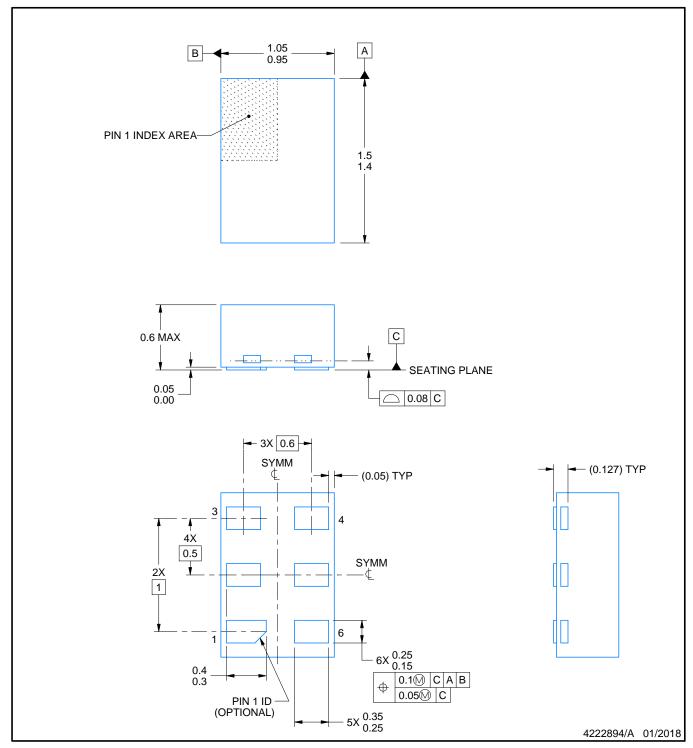


Images above are just a representation of the package family, actual package may vary. Refer to the product data sheet for package details.







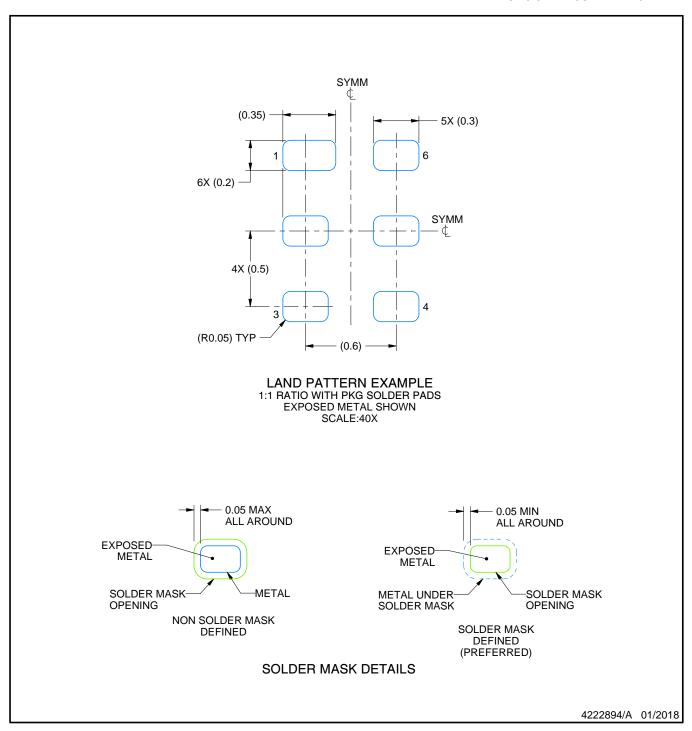


NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

 2. This drawing is subject to change without notice.

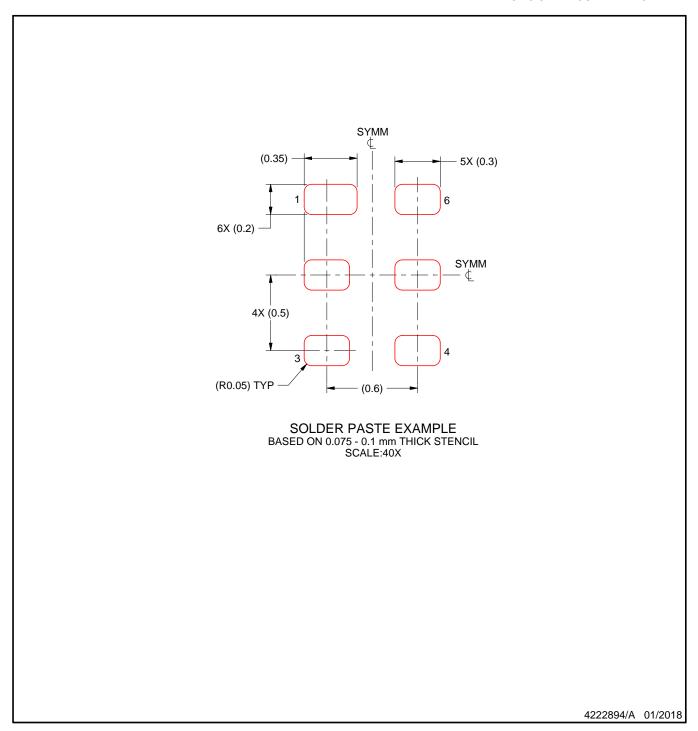




NOTES: (continued)

3. For more information, see QFN/SON PCB application report in literature No. SLUA271 (www.ti.com/lit/slua271).



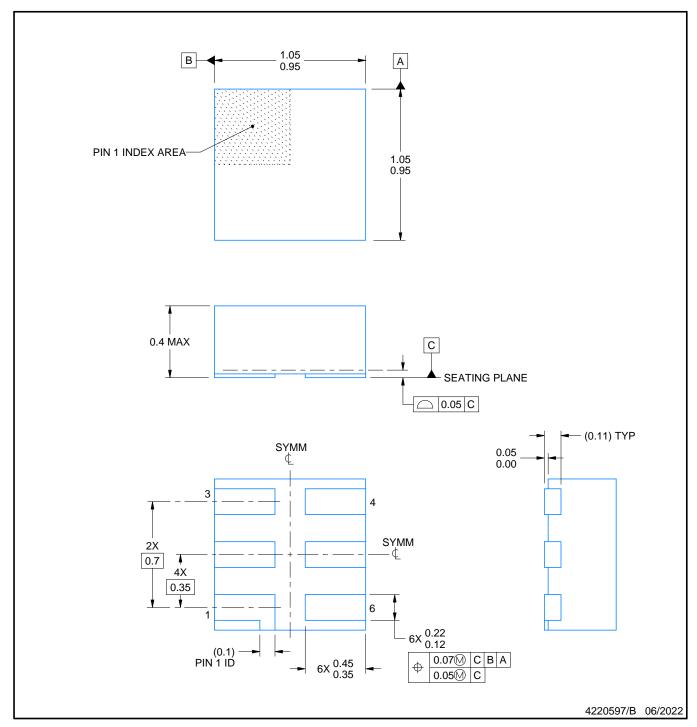


NOTES: (continued)

Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.







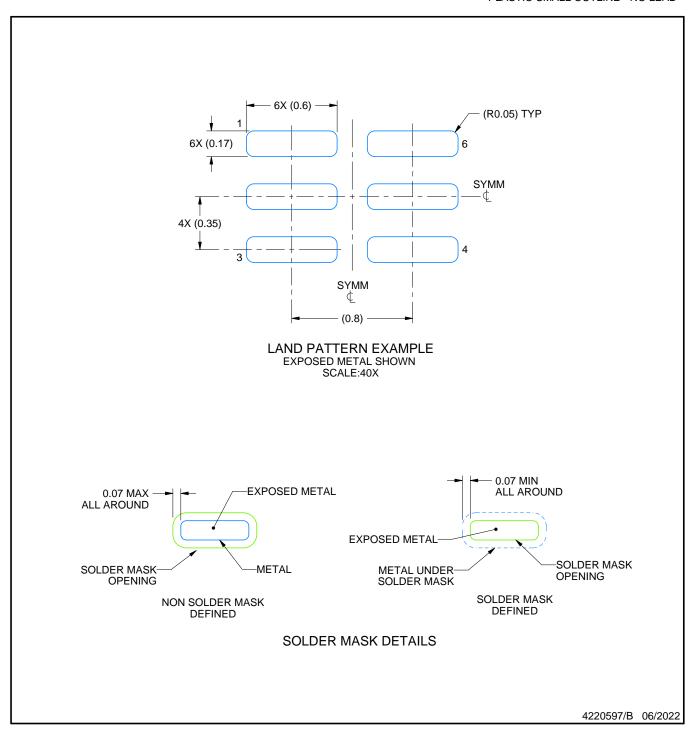
NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

 2. This drawing is subject to change without notice.

 3. Reference JEDEC registration MO-287, variation X2AAF.

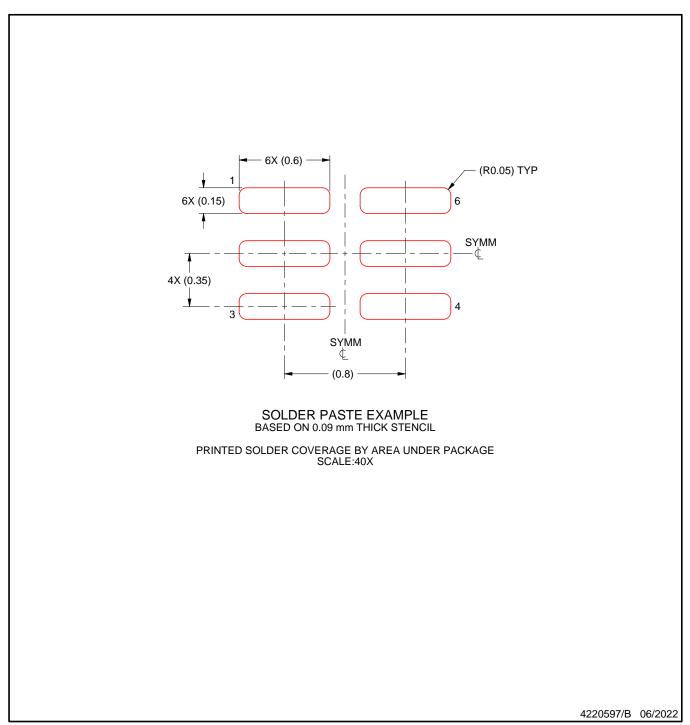




NOTES: (continued)

4. For more information, see Texas Instruments literature number SLUA271 (www.ti.com/lit/slua271).



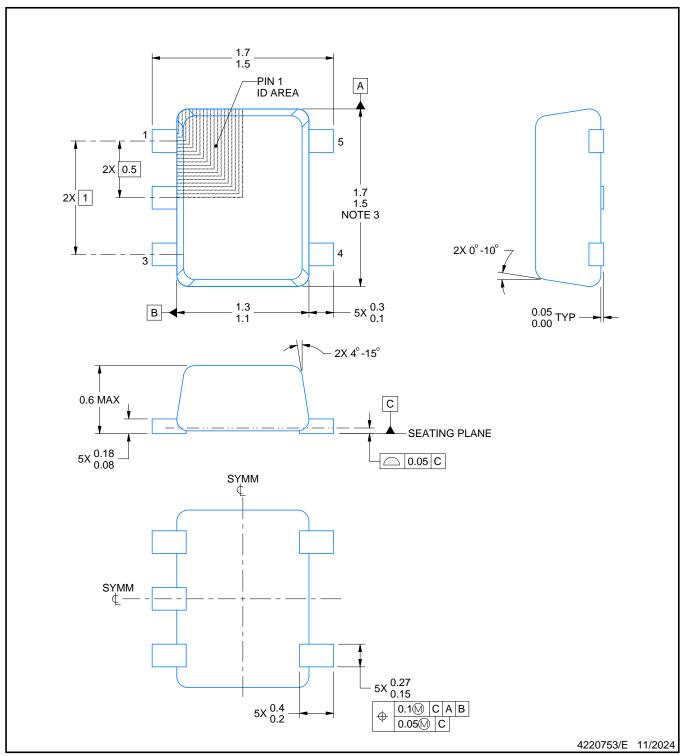


4. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.





PLASTIC SMALL OUTLINE

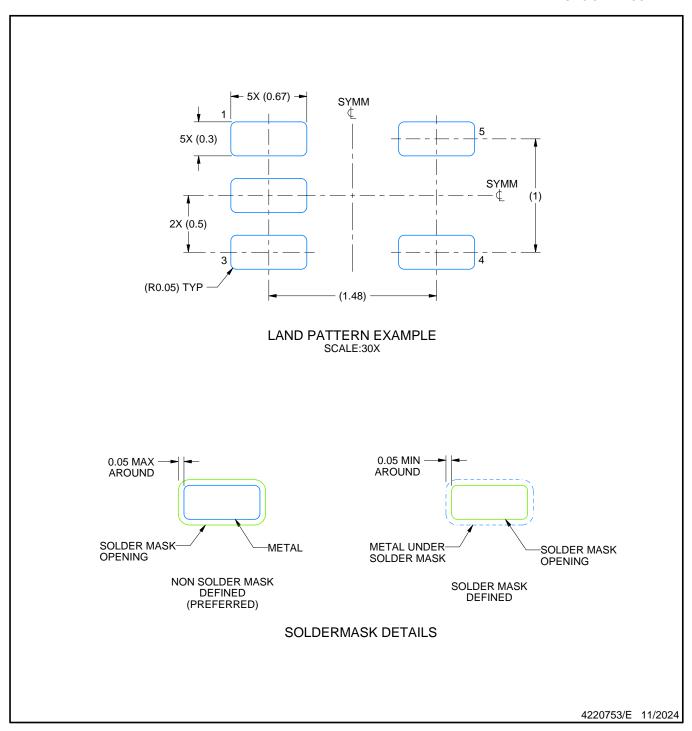


NOTES:

- All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
 This drawing is subject to change without notice.
 This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not
- exceed 0.15 mm per side.
 4. Reference JEDEC registration MO-293 Variation UAAD-1



PLASTIC SMALL OUTLINE

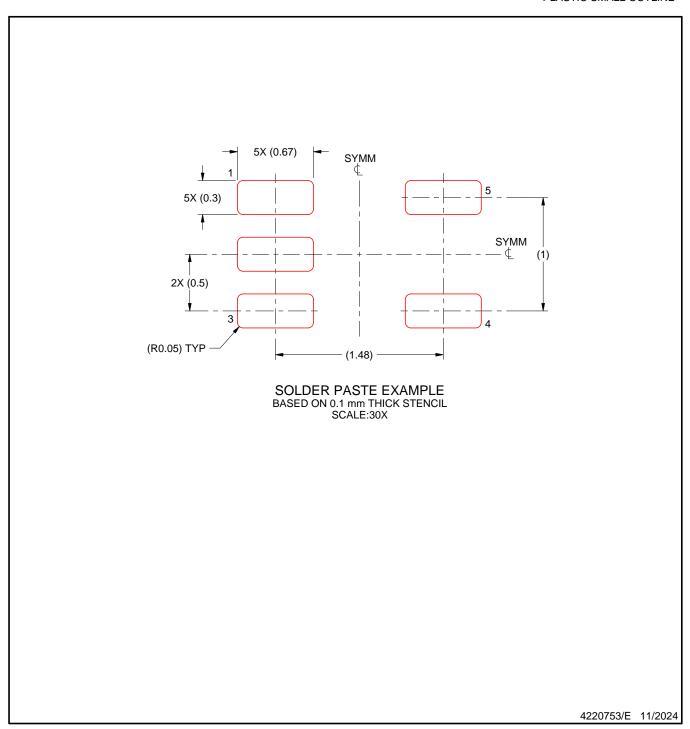


NOTES: (continued)

- 5. Publication IPC-7351 may have alternate designs.
- 6. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



PLASTIC SMALL OUTLINE



NOTES: (continued)

- 7. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 8. Board assembly site may have different recommendations for stencil design.





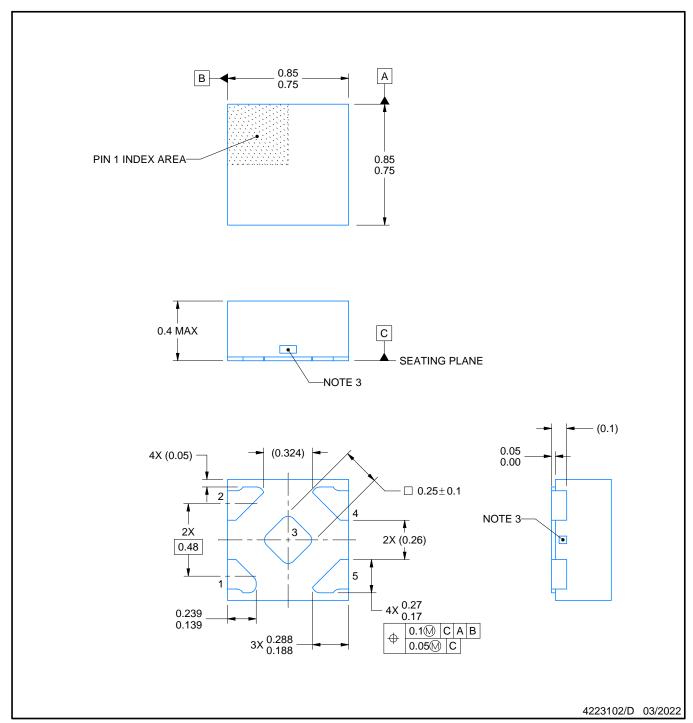
Images above are just a representation of the package family, actual package may vary. Refer to the product data sheet for package details.

4211218-3/D





PLASTIC SMALL OUTLINE - NO LEAD

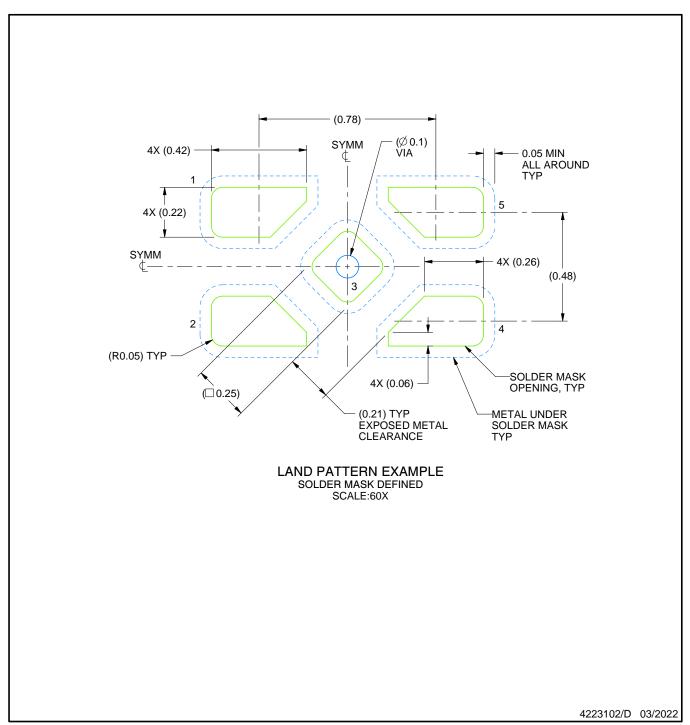


- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

 2. This drawing is subject to change without notice.
- 3. The size and shape of this feature may vary.



PLASTIC SMALL OUTLINE - NO LEAD

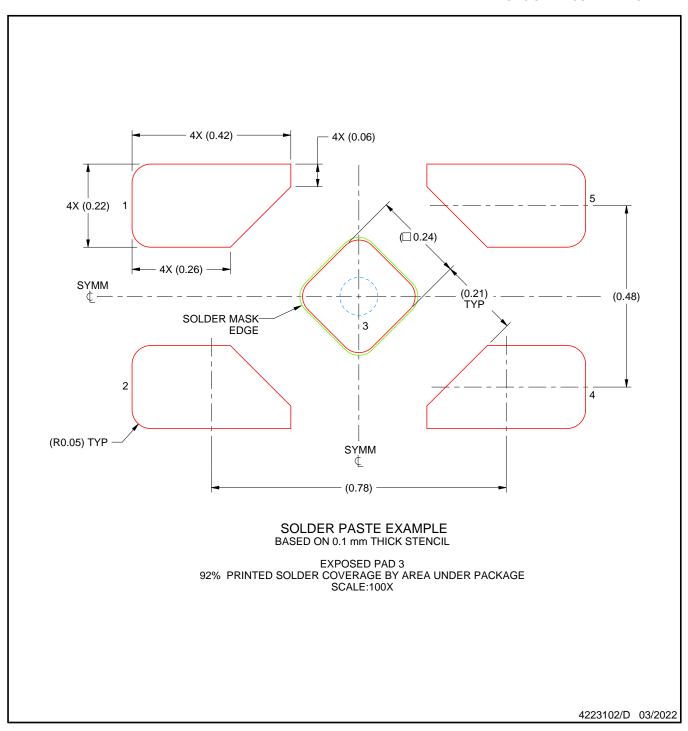


NOTES: (continued)

4. This package is designed to be soldered to a thermal pad on the board. For more information, refer to QFN/SON PCB application note in literature No. SLUA271 (www.ti.com/lit/slua271).



PLASTIC SMALL OUTLINE - NO LEAD

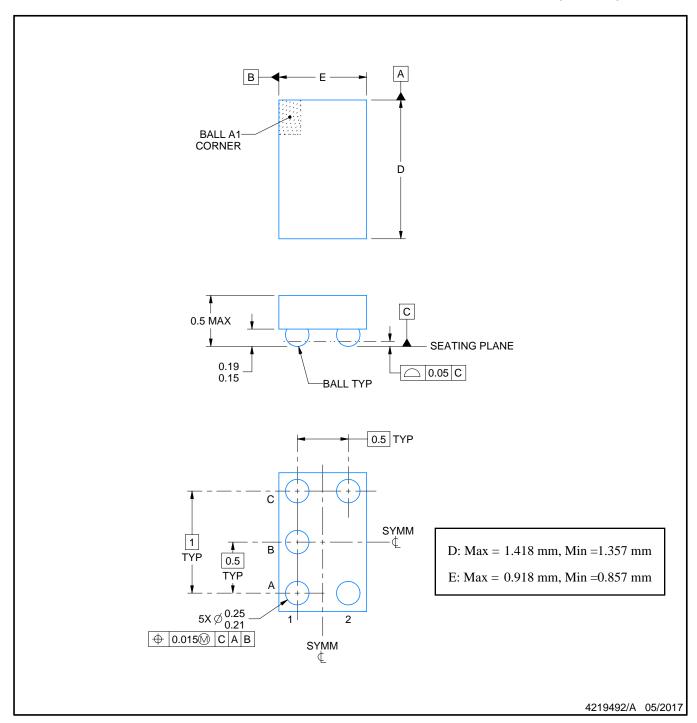


NOTES: (continued)

5. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.

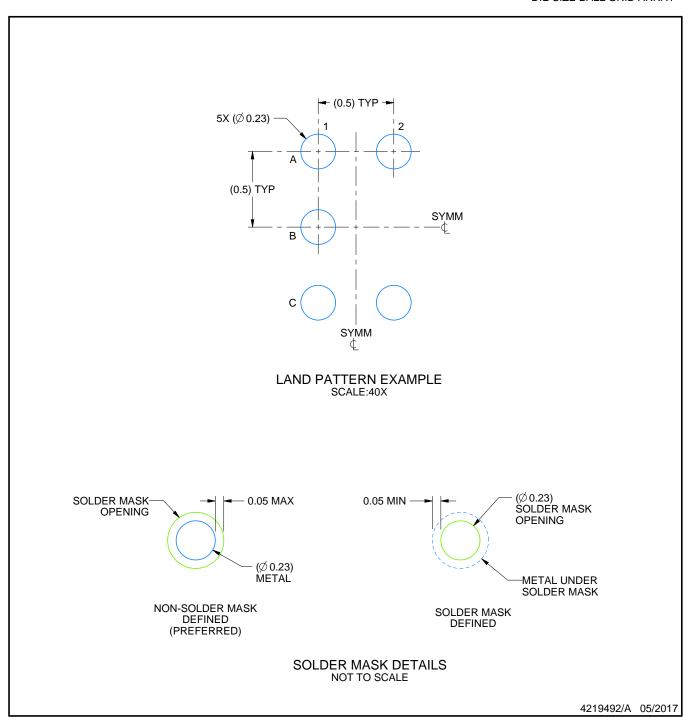






- All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
- 2. This drawing is subject to change without notice.

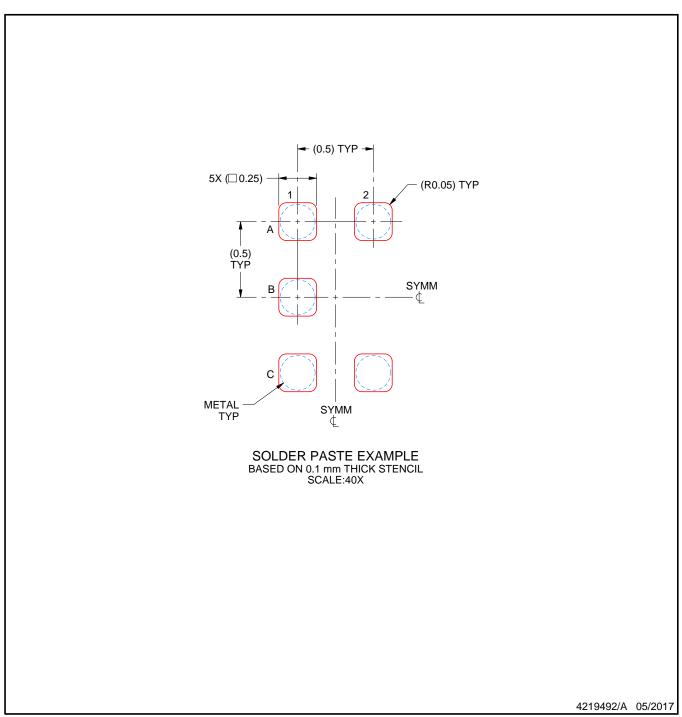




NOTES: (continued)

3. Final dimensions may vary due to manufacturing tolerance considerations and also routing constraints. For more information, see Texas Instruments literature number SNVA009 (www.ti.com/lit/snva009).





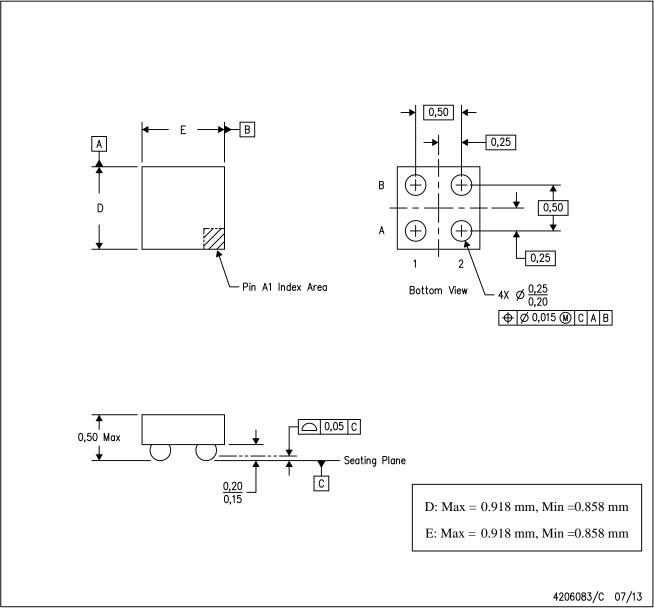
NOTES: (continued)

4. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release.



YZV (S-XBGA-N4)

DIE-SIZE BALL GRID ARRAY



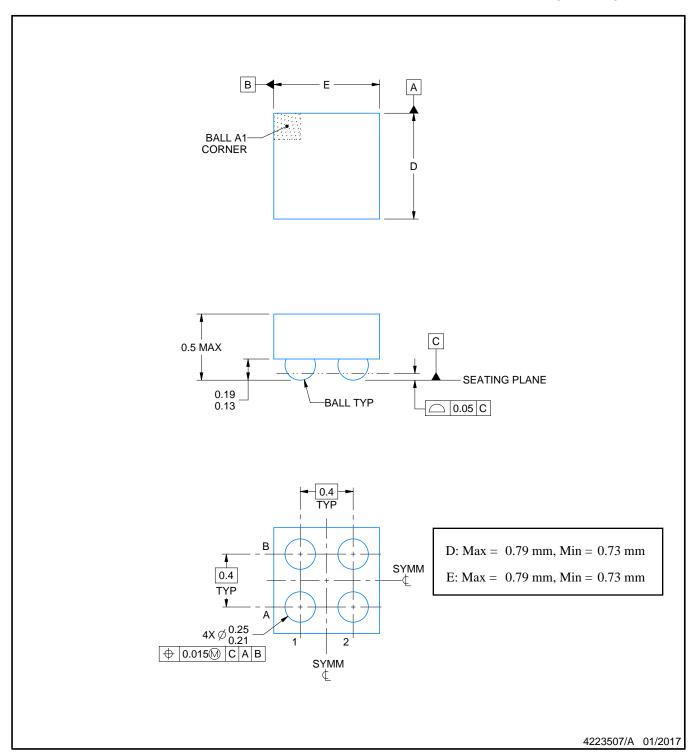
NOTES: A. All linear dimensions are in millimeters. Dimensioning and tolerancing per ASME Y14.5M—1994.

- B. This drawing is subject to change without notice.
- C. NanoFree™ package configuration.

NanoFree is a trademark of Texas Instruments.

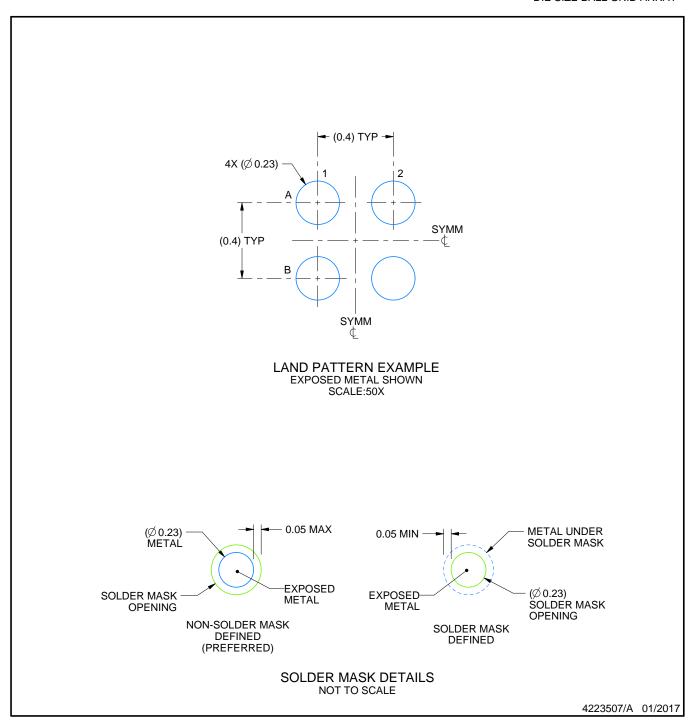






- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
 2. This drawing is subject to change without notice.

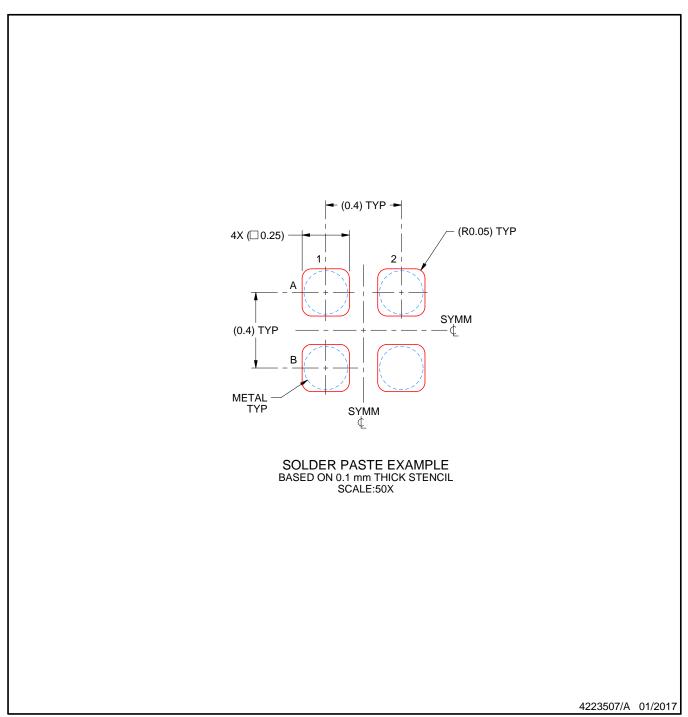




NOTES: (continued)

3. Final dimensions may vary due to manufacturing tolerance considerations and also routing constraints. For more information, see Texas Instruments literature number SNVA009 (www.ti.com/lit/snva009).





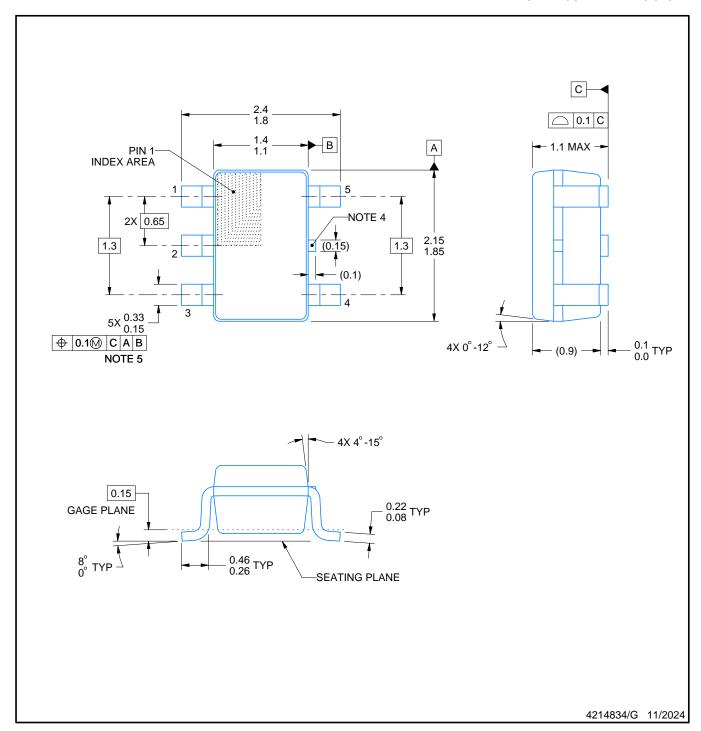
NOTES: (continued)

4. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release.





SMALL OUTLINE TRANSISTOR

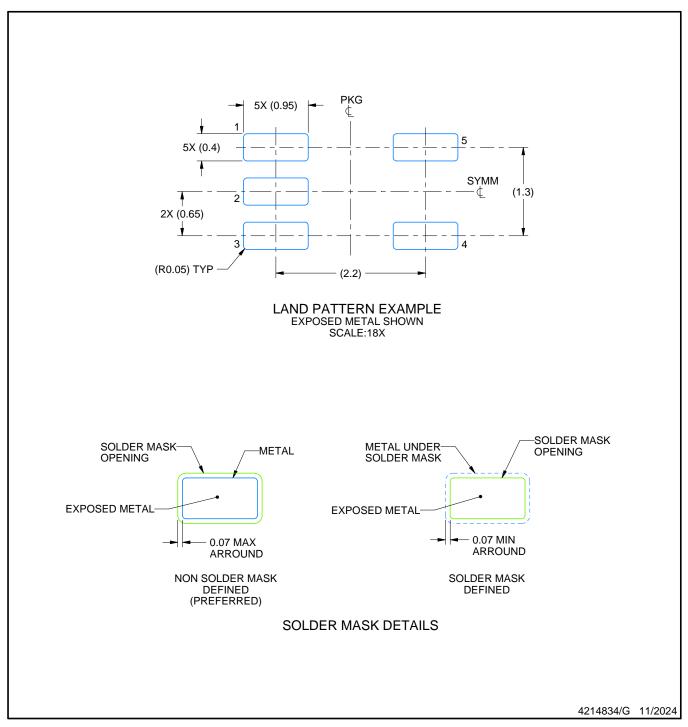


- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
 2. This drawing is subject to change without notice.
 3. Reference JEDEC MO-203.

- 4. Support pin may differ or may not be present.5. Lead width does not comply with JEDEC.
- 6. Body dimensions do not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.25mm per side



SMALL OUTLINE TRANSISTOR

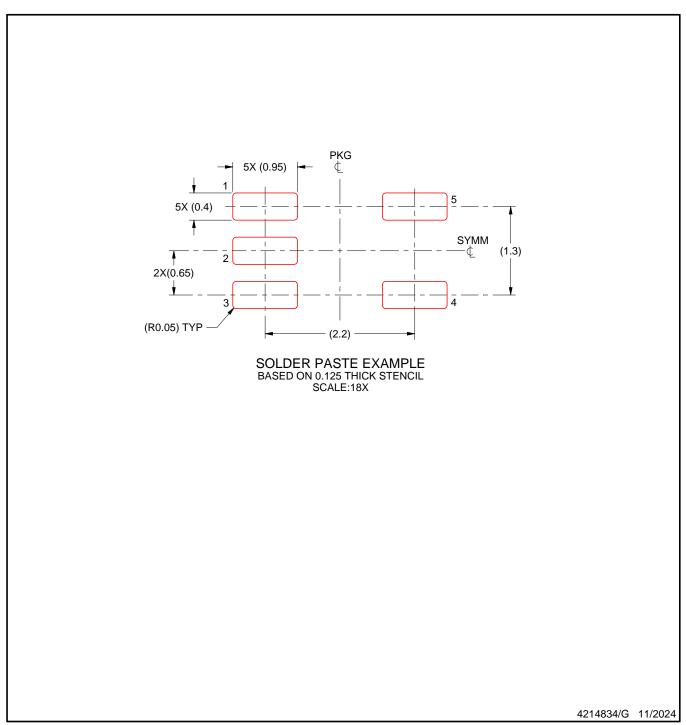


NOTES: (continued)

7. Publication IPC-7351 may have alternate designs.8. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



SMALL OUTLINE TRANSISTOR



NOTES: (continued)

- 9. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 10. Board assembly site may have different recommendations for stencil design.



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